

DATA SHEET

74LV00

Quad 2-input NAND gate

Product specification

1997 Feb 03

IC24 Data Handbook

Quad 2-input NAND gate

74LV00

FEATURES

- Wide operating voltage: 1.0 to 5.5 V
- Optimized for low voltage applications: 1.0 to 3.6 V
- Accepts TTL input levels between $V_{CC} = 2.7$ V and $V_{CC} = 3.6$ V
- Typical V_{OLP} (output ground bounce) < 0.8 V at $V_{CC} = 3.3$ V, $T_{amb} = 25^{\circ}\text{C}$
- Typical V_{OHV} (output V_{OH} undershoot) > 2 V at $V_{CC} = 3.3$ V, $T_{amb} = 25^{\circ}\text{C}$
- Output capability: standard
- I_{CC} category: SSI

DESCRIPTION

The 74LV00 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC/HCT00.

The 74LV00 provides the 2-input NAND function.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25^{\circ}\text{C}$; $t_r = t_f \leq 2.5$ ns

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t_{PHL} t_{PLH}	Propagation delay nA, nB to nY	$C_L = 15$ pF; $V_{CC} = 3.3$ V	7	ns
C_I	Input capacitance		3.5	pF
C_{PD}	Power dissipation capacitance per gate	See Notes 1 and 2	22	pF

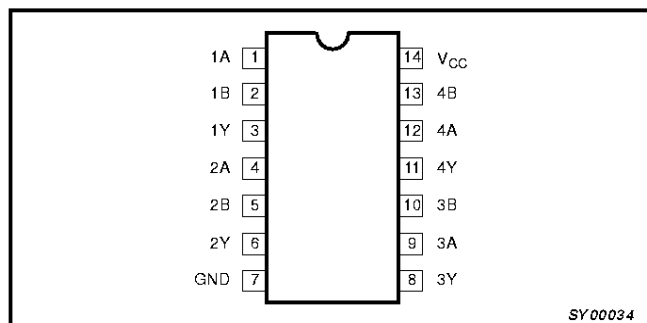
NOTES:

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW)
 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz; C_L = output load capacity in pF;
 f_o = output frequency in MHz; V_{CC} = supply voltage in V;
 $\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.
2. The condition is V_1 is $V_1 = \text{GND to } V_{CC}$.

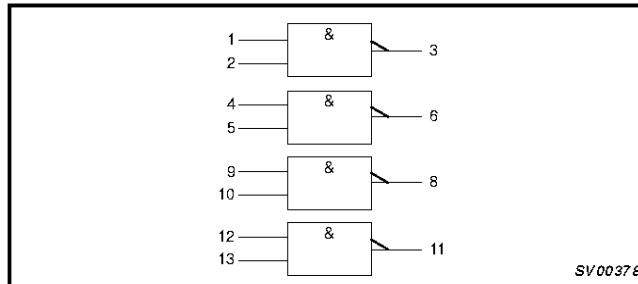
ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	PKG. DWG. #
14-Pin Plastic DIL	-40°C to +125°C	74LV00 N	74LV00 N	SOT27-1
14-Pin Plastic SO	-40°C to +125°C	74LV00 D	74LV00 D	SOT108-1
14-Pin Plastic SSOP Type II	-40°C to +125°C	74LV00 DB	74LV00 DB	SOT337-1
14-Pin Plastic TSSOP Type I	-40°C to +125°C	74LV00 PW	74LV00PW DH	SOT402-1

PIN CONFIGURATION



LOGIC SYMBOL (IEEE/IEC)



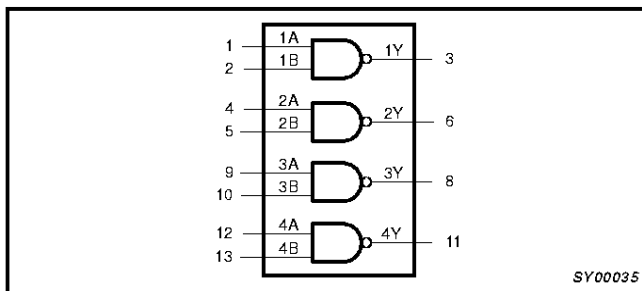
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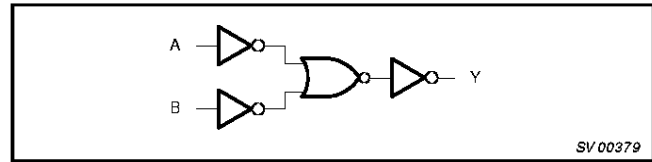
PIN DESCRIPTION

PIN NUMBER	SYMBOL	FUNCTION
1, 4, 9, 12	1A – 4A	Data inputs
2, 5, 10, 13	1B – 4B	Data inputs
3, 6, 8, 11	1Y – 4Y	Data outputs
7	GND	Ground (0 V)
14	V _{CC}	Positive supply voltage

LOGIC SYMBOL



LOGIC DIAGRAM (ONE GATE)



FUNCTION TABLE

INPUTS		OUTPUTS
nA	nB	nY
L	L	H
L	H	H
H	L	H
H	H	L

NOTES:

- H = HIGH voltage level
- L = LOW voltage level

ABSOLUTE MAXIMUM RATINGS^{1, 2}

In accordance with the Absolute Maximum Rating System (IEC 134). Voltages are referenced to GND (ground = 0V).

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +7.0	V
±I _{IK}	DC input diode current	V _I < -0.5 or V _I > V _{CC} + 0.5V	20	mA
±I _{OK}	DC output diode current	V _O < -0.5 or V _O > V _{CC} + 0.5V	50	mA
±I _O	DC output source or sink current – standard outputs – bus driver outputs	-0.5V < V _O < V _{CC} + 0.5V	25 35	mA
±I _{GND} , ±I _{CC}	DC V _{CC} or GND current for types with – standard outputs – bus driver outputs		50 70	mA
T _{stg}	Storage temperature range		-65 to +150	°C
P _{TOT}	Power dissipation per package – plastic DIL – plastic mini-pack (SO) – plastic shrink mini-pack (SSOP and TSSOP)	for temperature range: -40 to +125°C above +70°C derate linearly with 12 mW/K above +70°C derate linearly with 8 mW/K above +60°C derate linearly with 5.5 mW/K	750 500 400	mW

NOTES:

1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
2. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

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RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CC}	DC supply voltage	See Note 1	1.0	3.3	5.5	V
V _I	Input voltage		0	–	V _{CC}	V
V _O	Output voltage		0	–	V _{CC}	V
T _{amb}	Operating ambient temperature range in free air	See DC and AC characteristics per device	–40 –40		+85 +125	°C
t _r , t _f	Input rise and fall times except for Schmitt-trigger inputs	V _{CC} = 1.0V to 2.0V V _{CC} = 2.0V to 2.7V V _{CC} = 2.7V to 3.6V V _{CC} = 3.6V to 5.5V	– – – –	– – – –	500 200 100 50	ns/V

NOTE:

1. The LV is guaranteed to function down to V_{CC} = 1.0V (input levels GND or V_{CC}); DC characteristics are guaranteed from V_{CC} = 1.2V to V_{CC} = 5.5V.

DC ELECTRICAL CHARACTERISTICS

Over recommended operating conditions. Voltages are referenced to GND (ground = 0V).

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS					UNIT
			–40°C to +85°C			–40°C to +125°C		
			MIN	TYP ¹	MAX	MIN	MAX	
V _{IH}	HIGH level Input voltage	V _{CC} = 1.2V	V _{CC}	0.6		V _{CC}		V
		V _{CC} = 2.0V	1.4		1.4			
		V _{CC} = 2.7 to 3.6V	2.0		2.0			
		V _{CC} = 4.5 to 5.5V	0.7 * V _{CC}		0.7 * V _{CC}			
V _{IL}	LOW level Input voltage	V _{CC} = 1.2V		0.4	GND		GND	V
		V _{CC} = 2.0V			0.6		0.6	
		V _{CC} = 2.7 to 3.6V			0.8		0.8	
		V _{CC} = 4.5 to 5.5			0.3 * V _{CC}		0.3 * V _{CC}	
V _{OH}	HIGH level output voltage; all outputs	V _{CC} = 1.2V; V _I = V _{IH} or V _{IL} ; –I _O = 100µA		1.2				V
		V _{CC} = 2.0V; V _I = V _{IH} or V _{IL} ; –I _O = 100µA	1.8	2.0		1.8		
		V _{CC} = 2.7V; V _I = V _{IH} or V _{IL} ; –I _O = 100µA	2.5	2.7		2.5		
		V _{CC} = 3.0V; V _I = V _{IH} or V _{IL} ; –I _O = 100µA	2.8	3.0		2.8		
		V _{CC} = 4.5V; V _I = V _{IH} or V _{IL} ; –I _O = 100µA	4.3	4.5		4.3		
V _{OH}	HIGH level output voltage; STANDARD outputs	V _{CC} = 3.0V; V _I = V _{IH} or V _{IL} ; –I _O = 6mA	2.40	2.82		2.20		V
		V _{CC} = 4.5V; V _I = V _{IH} or V _{IL} ; –I _O = 12mA	3.60	4.20		3.50		
V _{OH}	HIGH level output voltage; BUS driver outputs	V _{CC} = 3.0V; V _I = V _{IH} or V _{IL} ; –I _O = 8mA	2.40	2.82		2.20		V
		V _{CC} = 4.5V; V _I = V _{IH} or V _{IL} ; –I _O = 16mA	3.60	4.20		3.50		
V _{OL}	LOW level output voltage; all outputs	V _{CC} = 1.2V; V _I = V _{IH} or V _{IL} ; I _O = 100µA		0				V
		V _{CC} = 2.0V; V _I = V _{IH} or V _{IL} ; I _O = 100µA		0	0.2		0.2	
		V _{CC} = 2.7V; V _I = V _{IH} or V _{IL} ; I _O = 100µA		0	0.2		0.2	
		V _{CC} = 3.0V; V _I = V _{IH} or V _{IL} ; I _O = 100µA		0	0.2		0.2	
		V _{CC} = 4.5V; V _I = V _{IH} or V _{IL} ; I _O = 100µA		0	0.2		0.2	
V _{OL}	LOW level output voltage; STANDARD outputs	V _{CC} = 3.0V; V _I = V _{IH} or V _{IL} ; I _O = 6mA		0.25	0.40		0.50	V
		V _{CC} = 4.5V; V _I = V _{IH} or V _{IL} ; I _O = 12mA		0.35	0.55		0.65	
V _{OL}	LOW level output voltage; BUS driver outputs	V _{CC} = 3.0V; V _I = V _{IH} or V _{IL} ; I _O = 8mA		0.20	0.40		0.50	V
		V _{CC} = 4.5V; V _I = V _{IH} or V _{IL} ; I _O = 16mA		0.35	0.55		0.65	
I _I	Input leakage current	V _{CC} = 5.5V; V _I = V _{CC} or GND			1.0		1.0	µA
I _{oz}	3-State output OFF-state current	V _{CC} = 5.5V; V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND			5		10	µA

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DC ELECTRICAL CHARACTERISTICS (Continued)

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS					UNIT
			-40°C to +85°C			-40°C to +125°C		
			MIN	TYP ¹	MAX	MIN	MAX	
I _{CC}	Quiescent supply current; SSI	V _{CC} = 5.5V; V _I = V _{CC} or GND; I _O = 0			20.0		40	μA
	Quiescent supply current; flip-flops	V _{CC} = 5.5V; V _I = V _{CC} or GND; I _O = 0			20.0		80	
I _{CC}	Quiescent supply current; MSI	V _{CC} = 5.5V; V _I = V _{CC} or GND; I _O = 0			20.0		160	μA
	Quiescent supply current; LSI	V _{CC} = 5.5V; V _I = V _{CC} or GND; I _O = 0			500		1000	
ΔI _{CC}	Additional quiescent supply current	V _{CC} = 2.7V to 3.6V; V _I = V _{CC} - 0.6V			500		850	μA

NOTE:

1. All typical values are measured at T_{amb} = 25°C.

AC CHARACTERISTICS

GND = 0V; t_r = t_f = 2.5ns; C_L = 50pF; R_L = 500Ω

SYMBOL	PARAMETER	WAVEFORM	CONDITION	LIMITS					UNIT
				-40 to +85 °C			-40 to +125 °C		
				MIN	TYP ¹	MAX	MIN	MAX	
t _{PHL/PLH}	Propagation delay nA, nB to nY	Figures 1, 2	V _{CC} (V)						
			1.2		45				
			2.0		15	26		31	
			2.7		11	18		23	
			3.0 to 3.6		9 ²	15		18	
4.5 to 5.5		6.5 ³	11		14				

NOTES:

1. Unless otherwise stated, all typical values are measured at T_{amb} = 25°C.

2. Typical values are measured at V_{CC} = 3.3 V.

3. Typical values are measured at V_{CC} = 5.0 V.

AC WAVEFORMS

V_M = 1.5 V at V_{CC} ≥ 2.7 V and ≤ 3.6 V;

V_M = 0.5 V × V_{CC} at < 2.7 V and ≥ 4.5 V;

V_{OH} are the typical output voltage drop that occur with the output load.

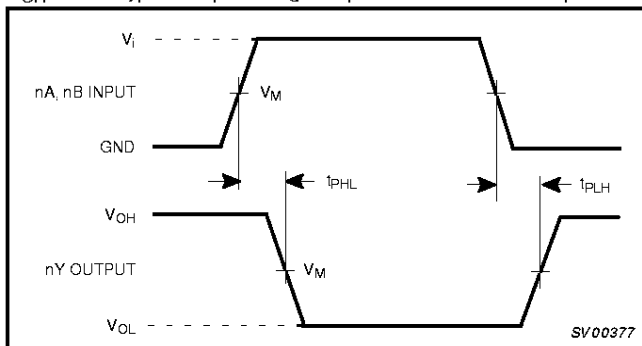


Figure 1. Input (nA, nB) to output (nY) propagation delays

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TEST CIRCUIT

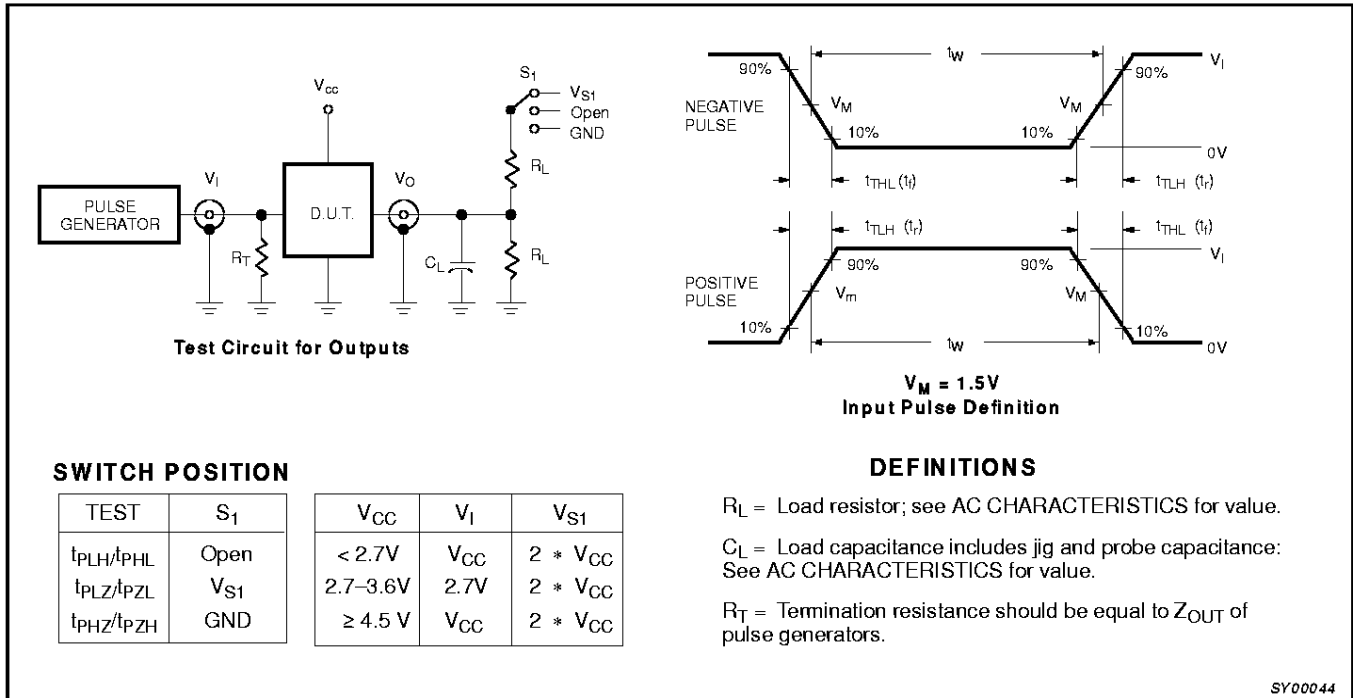


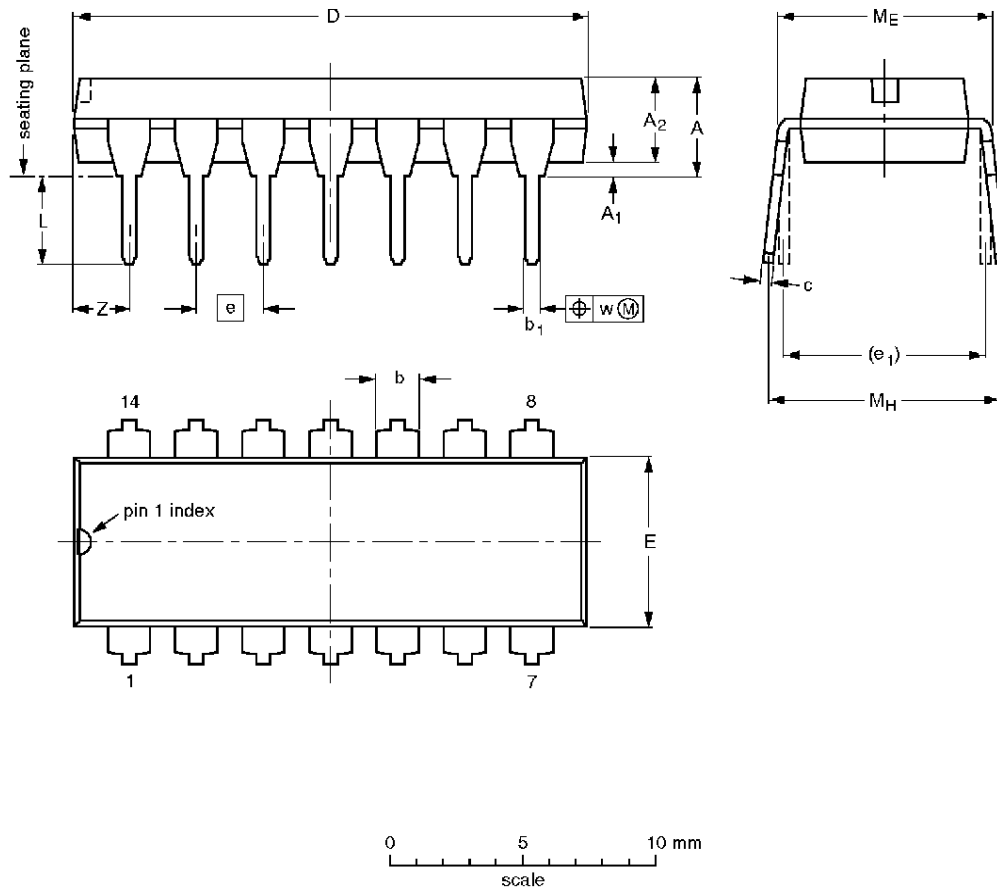
Figure 2. Load circuitry for switching times.

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DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	M _E	M _H	w	z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.020	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

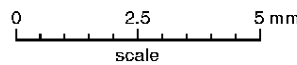
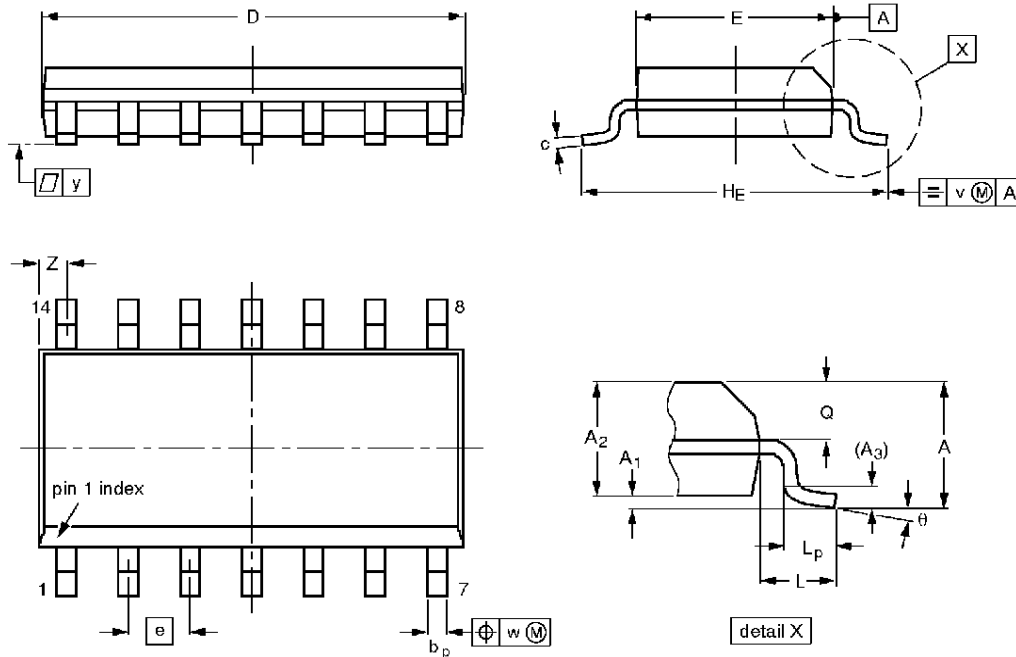
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT27-1	050G04	MO-001AA				92-11-17 95-03-11

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SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	HE	L	L _p	Q	v	w	y	z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.0098 0.0039	0.057 0.049	0.01	0.019 0.014	0.0098 0.0075	0.35 0.34	0.16 0.15	0.050	0.24 0.23	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

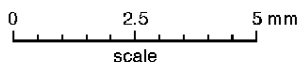
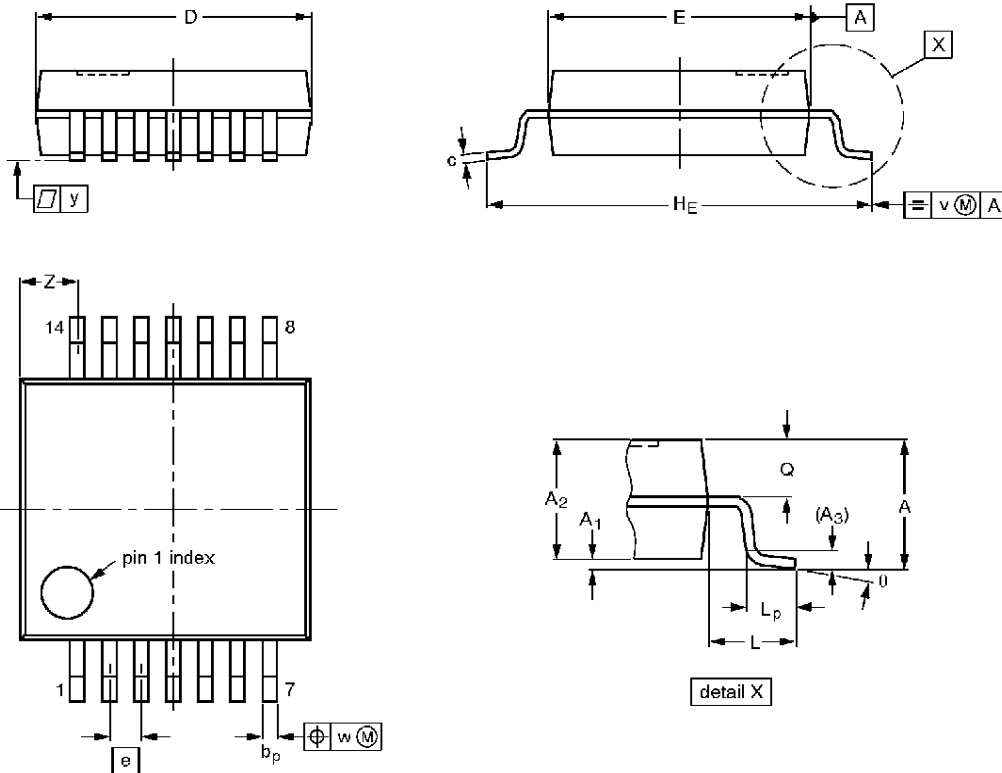
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT108-1	076E06S	MS-012AB				91-08-10 95-01-23

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SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

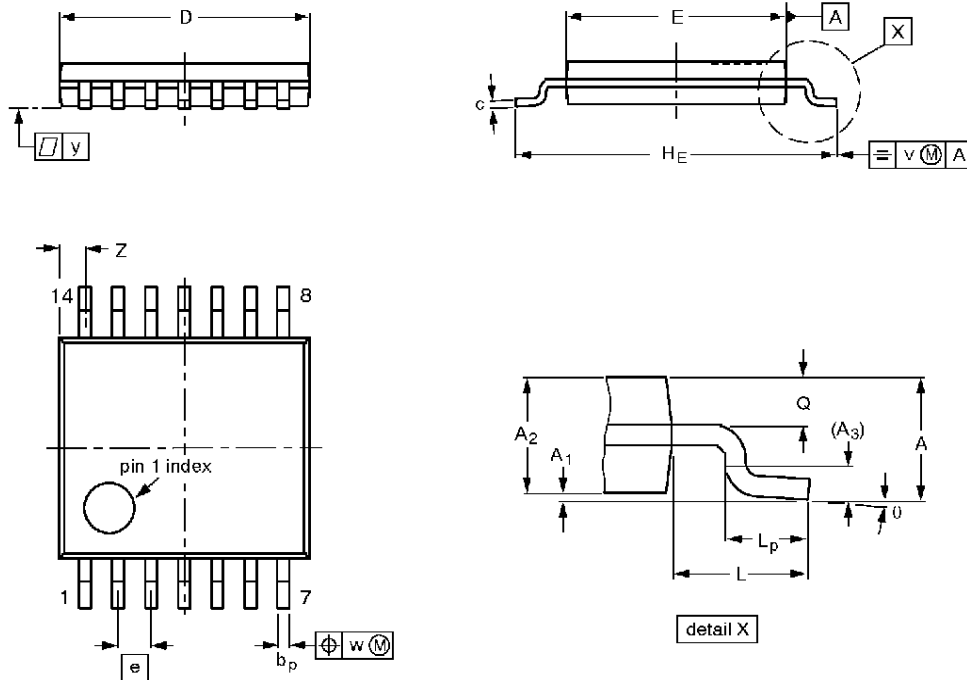
OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT337-1		MO-150AB			95-02-04 96-01-18

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TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽²⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT402-1		MO-153				94-07-12 95-04-04

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NOTES

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DEFINITIONS

Data Sheet Identification	Product Status	Definition
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